MOS-TECH Semiconductor Co.,LTD
臺灣茂鈿半導體股份有限公司

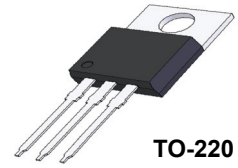
MT3240
N-Channel Power MOSFET
40V, 190A, 2.4mΩ

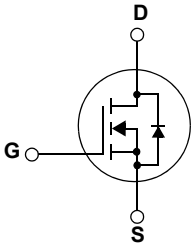
Features

- $R_{DS(on)}$ = 2.4mΩ (Typ.)@ V_{GS} = 10V, I_D = 80A
- $Q_{g(tot)}$ = 163nC (Typ.)@ V_{GS} = 10V
- Low Miller Charge
- Low Q_{RR} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- RoHS Compliant

Application

- Automotive Engine Control
- Powertrain Management
- Motors, Solenoids
- Electronic Steering
- Integrated Starter/ Alternator
- Distributed Power Architectures and VRMs
- Primary Switch for 12V Systems





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain to Source Voltage		40	V
V_{GSS}	Gate to Source Voltage		±20	V
I_D	Drain Current	- Continuous (T_C = 25°C, Silicon Limited) - Continuous (T_C = 100°C, Silicon Limited) - Continuous (T_C = 25°C, Package Limited)	190* 134* 100	A
I_{DM}	Drain Current	- Pulsed (Note 1)	750	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	1400	mJ
P_D	Power Dissipation	(T_C = 25°C)	220	W
		- Derate above 25°C	2.04	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

*Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 100A.

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.68	°C/W
$R_{\theta CS}$	Thermal Resistance, Case to Sink (Typ.)	0.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
MT3240	MT3240	TO-220	N/A	N/A	50units

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions		Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA		40	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 32V		--	--	1	μA
		V_{GS} = 0V	T_C = 150°C	--	--	250	μA
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20V		--	--	±100	nA
On Characteristics							
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA		1	--	3	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 4.5V, I_D = 80A		--	2.6	2.8	mΩ
		V_{GS} = 10V, I_D = 80A		--	2.4	2.6	
		V_{GS} = 10V, I_D = 80A, T_C = 175°C		--	3.00	4.4	
Dynamic Characteristics							
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz		--	6500	6740	pF
C_{oss}	Output Capacitance			--	916	950	pF
C_{rss}	Reverse Transfer Capacitance			--	780	800	pF
R_G	Gate Resistance	V_{GS} = 0.5V, f = 1MHz		--	1.1	--	Ω
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{GS} = 0V to 10V	V_{DD} = 20V, I_D = 80A, I_g = 1.0mA	--	163	180	nC
$Q_{g(2)}$	Threshold Gate Charge	V_{GS} = 0V to 2V		--	32.5	--	nC
Q_{gs}	Gate to Source Gate Charge			--	31	--	nC
Q_{gs2}	Gate Charge Threshold to Plateau			--	16.5	--	nC
Q_{gd}	Gate to Drain “Miller” Charge			--	64	--	nC
Switching Characteristics (V_{GS} = 10V)							
t_{ON}	Turn-On Time	V_{DD} = 20V,I_D = 80A, V_{GS} = 10V, R_{GEN} = 7Ω		--	175	360	ns
$t_{d(on)}$	Turn-On Delay Time			--	43	95	ns
t_r	Rise Time			--	130	275	ns
$t_{d(off)}$	Turn-Off Delay Time			--	435	875	ns
t_f	Fall Time			--	290	590	ns
t_{OFF}	Turn-Off Time			--	730	870	ns
Drain-Source Diode Characteristics and Maximum Ratings							
V_{SD}	Source to Drain Diode Voltage	I_{SD} = 80A		--	--	1.25	V
		I_{SD} = 40A		--	--	1.0	V
t_{rr}	Reverse Recovery Time	I_{SD} = 75A, dI_{SD}/dt = 100A/μs		--	59	--	ns
Q_{RR}	Reverse Recovery Charge	I_{SD} = 75A, dI_{SD}/dt = 100A/μs		--	77	--	nC

NOTES:

1: Pulse width limited by maximum junction temperature.

2: Starting T_J = 25°C, L = 1mH, I_{AS} = 58A, V_{DD} = 36V, V_{GS} = 10V.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

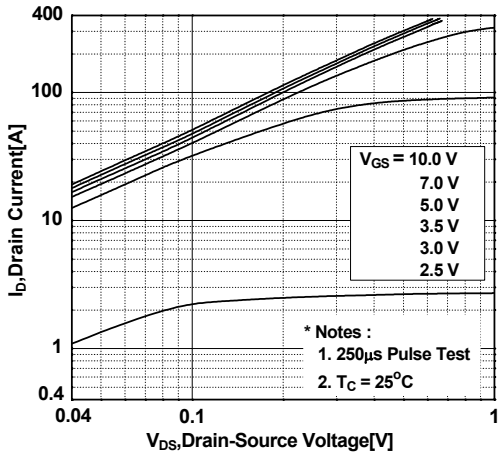


Figure 2. Transfer Characteristics

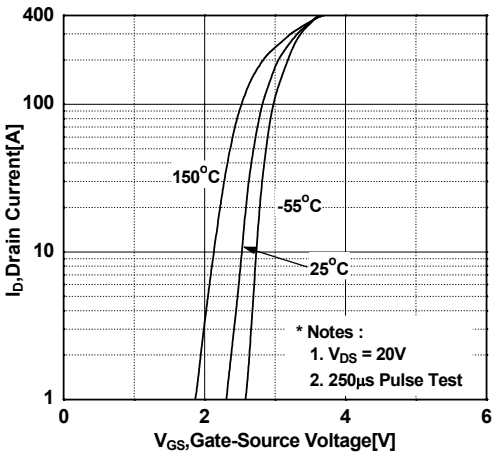


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

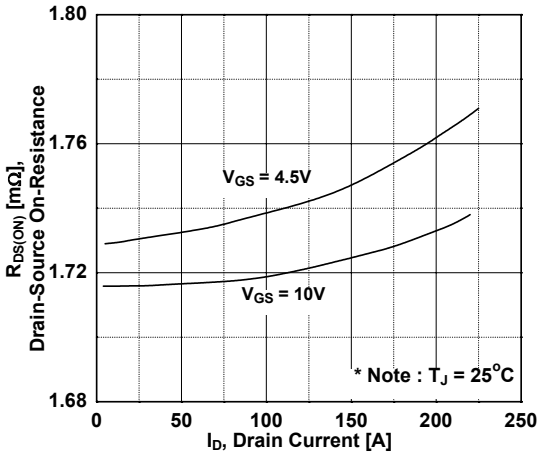


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

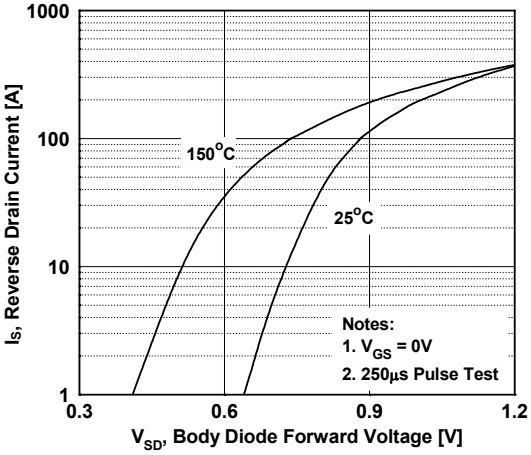


Figure 5. Capacitance Characteristics

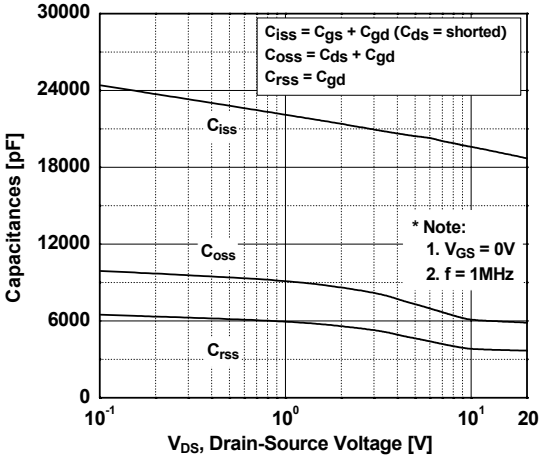
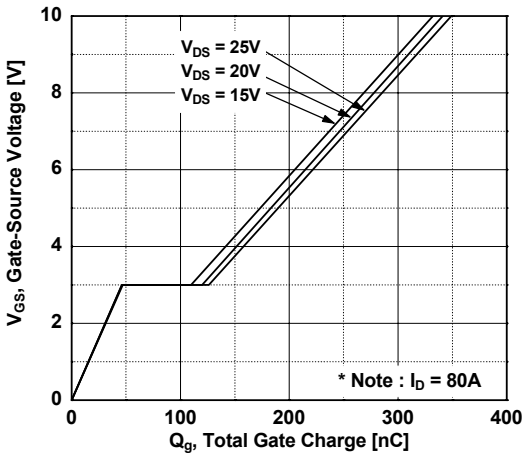


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

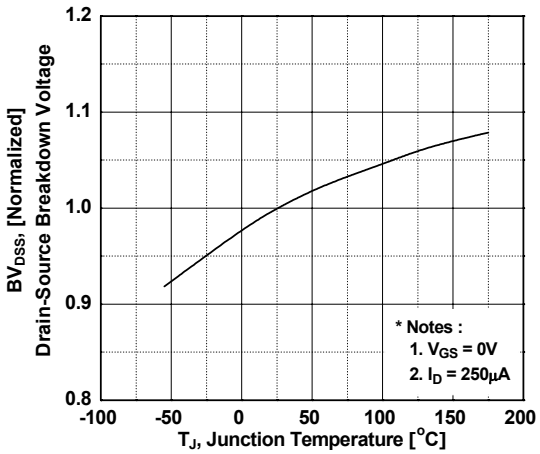


Figure 8. On-Resistance Variation vs. Temperature

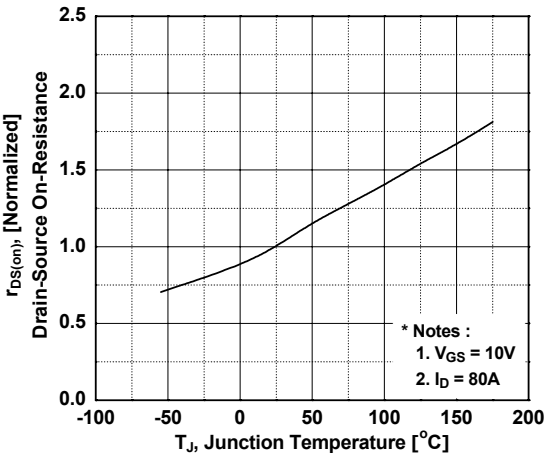


Figure 9. Unclamped Inductive Switching Capability

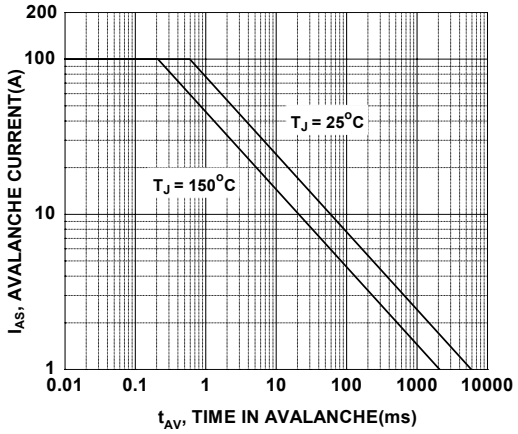


Figure 10. Safe Operating Area

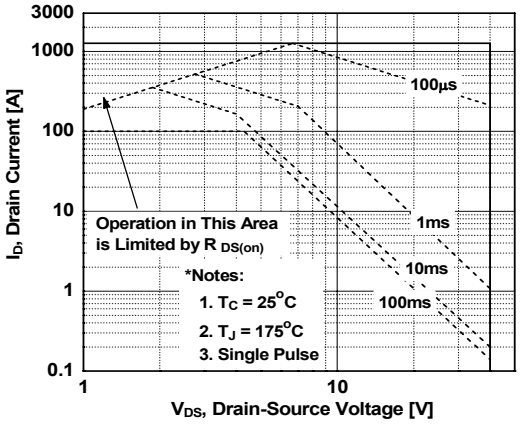
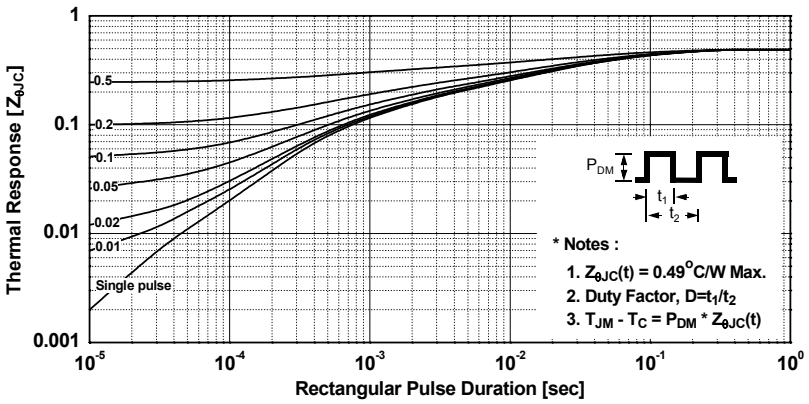
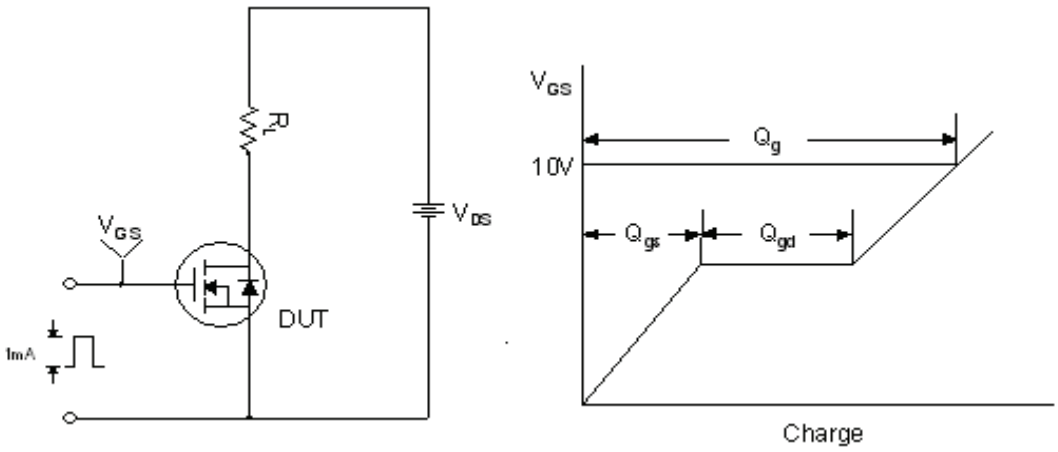


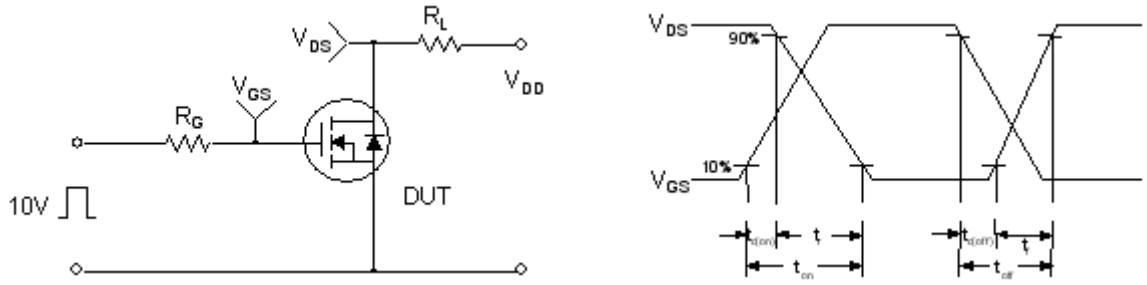
Figure 11. Transient Thermal Response Curve



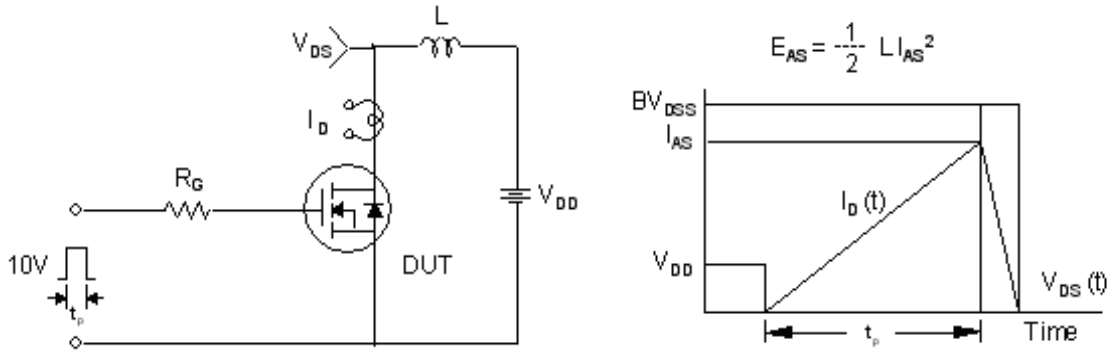
Gate Charge Test Circuit & Waveform



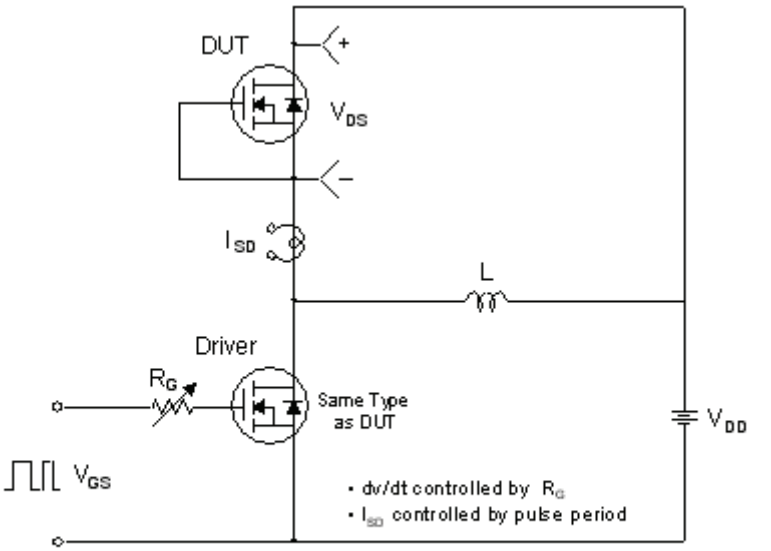
Resistive Switching Test Circuit & Waveforms

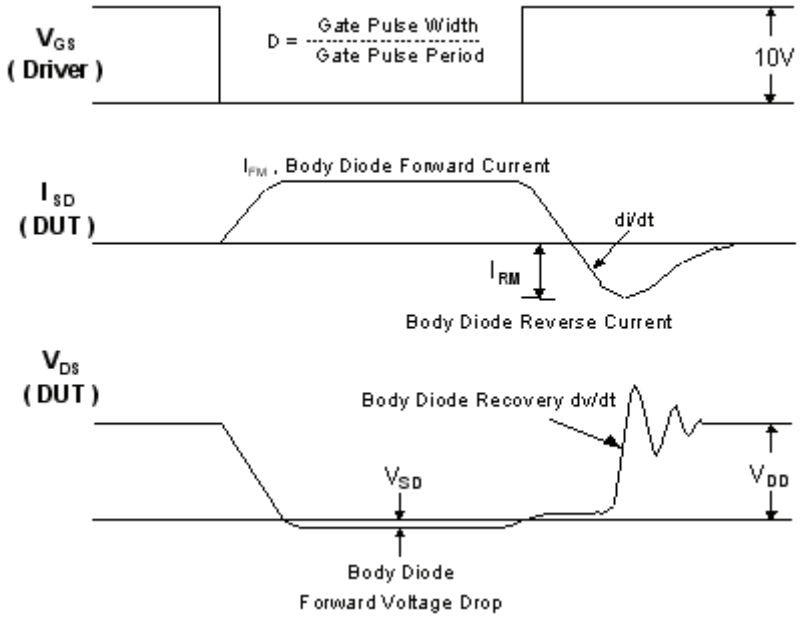


Unclamped Inductive Switching Test Circuit & Waveforms

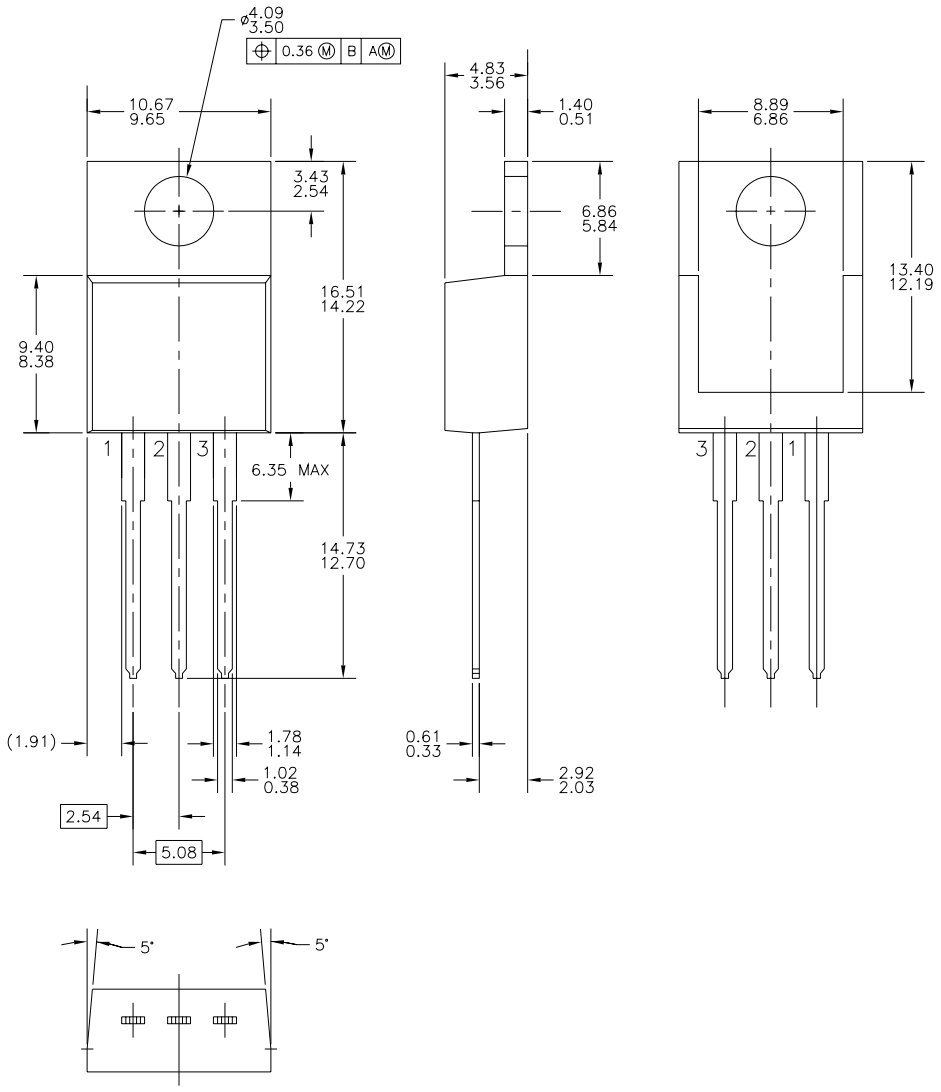


Peak Diode Recovery dv/dt Test Circuit & Waveforms





TO-220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3.50
0.36 M B A M
10.67
9.65
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9.40
8.38
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6.35 MAX
14.73
12.70
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1.02
0.38
2.54
5.08
4.83
3.56
1.40
0.51
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